ACE2N7002KU

N-Channel Enhancement Mode MOSFET

Description

The ACE2N7002KU is the N-Channel enhancement mode field effect transistors are produced using high cell density DMOS technology. These products have been designed to minimize on-state resistance while provide rugged, reliable, and fast switching performance. They can be used in most applications requiring up to 640mA DC and can deliver pulsed currents up to 950mA. These products are particularly suited for low voltage, low current applications such as small servo motor control, power MOSFET gate drivers, and other switching applications.

Features

- 60V/0.50A , $R_{DS(ON)}$= 2.0Ω@V_{GS}=10V
- 60V/0.20A , $R_{DS(ON)}$= 4.0Ω@V_{GS}=4.5V
- Super high density cell design for extremely low $R_{DS\ (ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOT-323 package design

Applications

- Drivers: Relays, Solenoids, Lamps, Hammers, Display, Memories, Transistors, etc.
- High saturation current capability. Direct Logic-Level Interface: TTL/CMOS
- Battery Operated Systems
- Solid-State Relays

Absolute Maximum Ratings

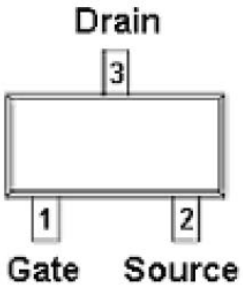
(T_A=25℃ Unless otherwise noted)

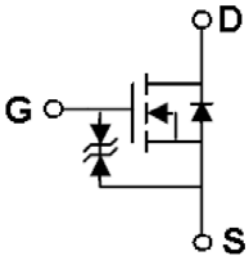
Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (T_J=150℃)	T_A=25℃	I_D	0.64	A
Pulsed Drain Current(*)		I_{DM}	0.95	A
Power Dissipation	T_A=25℃	P_D	1.35	A
Operating Junction Temperature		T_J	-55~150	W
Storage Temperature Range		T_{STG}	-55~150	°C
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	375	°C /W

(*) Pulse width limited by safe operating area

Packaging Type

SOT-323





Pin Description

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

Ordering information

ACE2N7002KU XX + H

- H: Halogen - free
- Pb - free
- XX: CM: SOT-323

ESD Capability Report

1. MM Test

Testing Item	ESD (MACHINE MODE) TEST
Method	ANSI/ESD S5.2-2009
Test Equipment	ZAPMASTER MK.2 SE
Laboratory Ambinence Condition	Temperature : 25℃ ±5℃
	Humidity : 55% ±5% RH

Curve Trace Criteria

Pin Combination	Force Voltage	Limit Current
G v.s. S	-100V ~ +1500V	1 μA

Curve Trace Result within 10% range

Test Result

Pin Combination	Sample Size	ESD Sensitivity
G(+) - S	5	+275 V
G(-) - S	5	-225 V

2. HBM Test

Testing Item	ESD (MACHINE MODE) TEST
Method	MIL-STD-883J/Method 3015.8
Test Equipment	ZAPMASTER MK.2 SE
Laboratory Ambinence Condition	Temperature : 25℃ ±5℃
	Humidity : 55% ±5% RH

Curve Trace Criteria

Pin Combination	Force Voltage	Limit Current
G v.s. S	-1500V ~ +8000V	1 μA

Curve Trace Result within 10% range

Test Result

Pin Combination	Sample Size	ESD Sensitivity
G(+) - S	5	+2500 V
G(-) - S	5	-2150V

3. CDM Test

Testing Item	ESD (MACHINE MODE) TEST
Method	ANSI/ESD S5.3.2-2008
Test Equipment	ZAPMASTER MK.2 SE
Laboratory Ambinence Condition	Temperature : 25℃ ±5℃
	Humidity : 55% ±5% RH

Curve Trace Criteria

Pin Combination	Force Voltage	Limit Current
G v.s. S	-100V ~ +15000V	1 μA

Curve Trace Result within 10% range

Test Result

Pin Combination	Sample Size	ESD Sensitivity
G(+) - S	5	+5500 V
G(-) - S	5	-900V

Electrical Characteristics

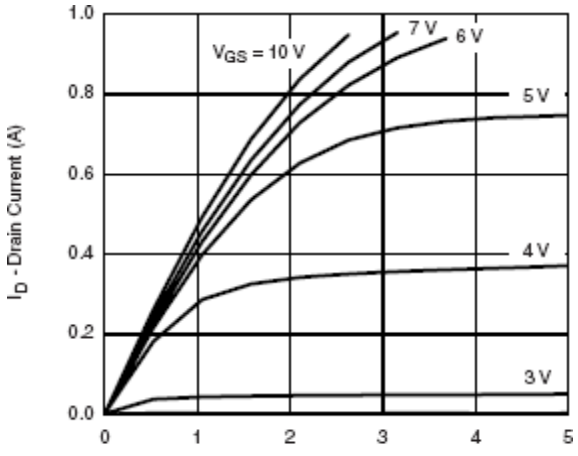
T_A=25℃, unless otherwise noted.

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250 uA	60			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	1.0	1.7	2.5	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±20V			±30	uA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V, V_{GS}=0V, T_J=25℃			10	uA
		V_{DS}=48V, V_{GS}=0V, T_J=70℃			100	
Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=0.5A			2.0	Ω
		V_{GS}=4.5V, I_D=0.2A			4.0	
Forward Trans Conductance	$gfs_{(1)}$	V_{DS}=10V, I_D=0.6A		0.6		S
Diode Forward Voltage	$V_{SD(1)}$	V_{GS}=0V, I_S=-0.45A			1.2	V
Dynamic						
Total Gate Charge	Q_g	V_{DD}=50V, V_{GS}=4.5V, I_D≡0.6A		1.0	1.6	nC
Gate-Source Charge	Q_{gs}			0.5		
Gate-Drain Charge	Q_{gd}			0.5		
Input Capacitance	Ciss	V_{DS} = 25V, f = 1 MHz, V_{GS} = 0		32	50	pF
Output Capacitance	Coss			8		
Reverse Transfer Capacitance	Crss			6		
Turn-On Time	td(on)	V_{DD}=30V, I_D≡0.6A, R_G=3.3Ω, V_{GS}=10V, R_D=52Ω		12		ns
	tr			10		
Turn-Off Time	td(off)			56		
	tf			29		

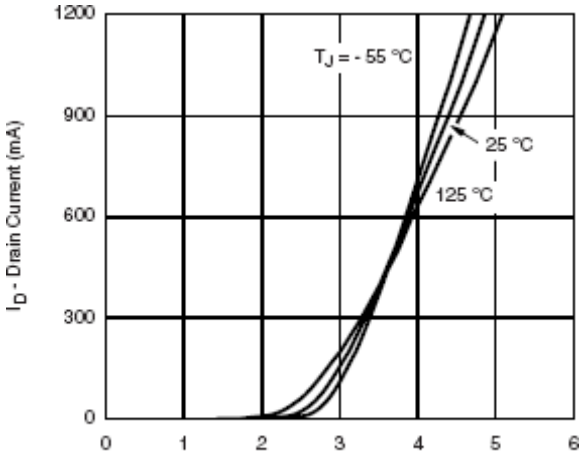
(1) Pulsed: Pulse duration = 300 μs, duty cycle 1.5%.

(2) Pulse width limited by safe operating area.

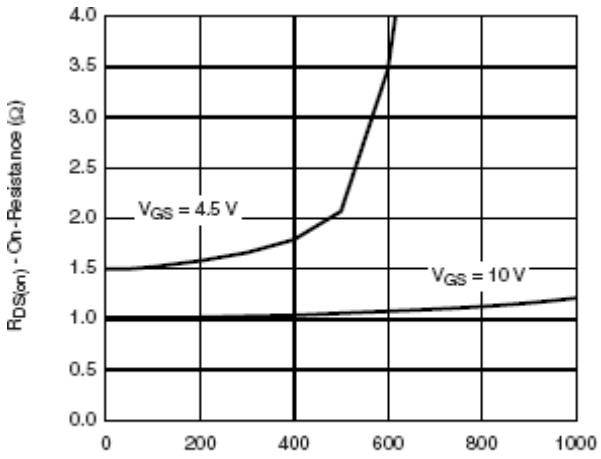
Typical Performance Characteristics



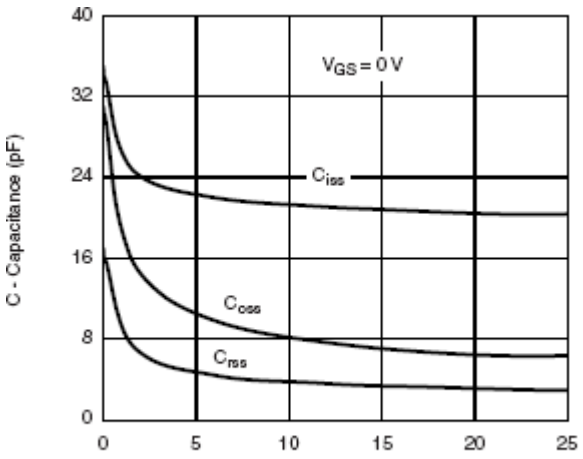
Output Characteristics



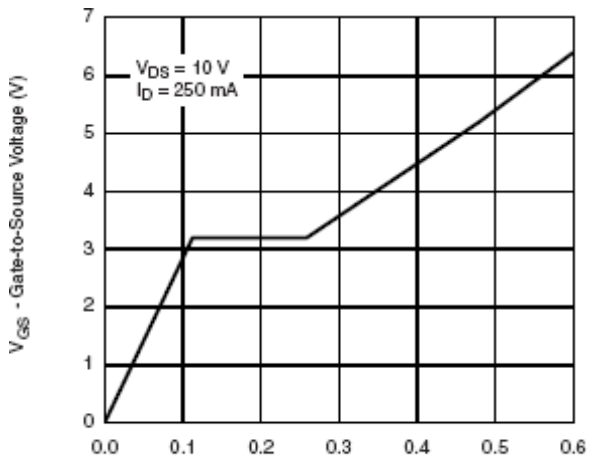
Transfer Characteristics



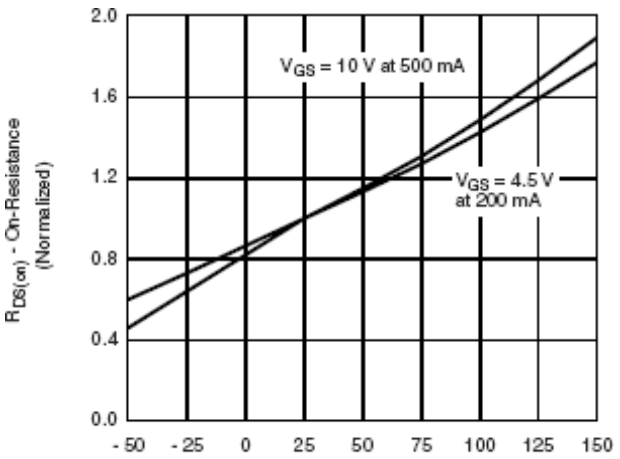
On-Resistance vs. Drain Current



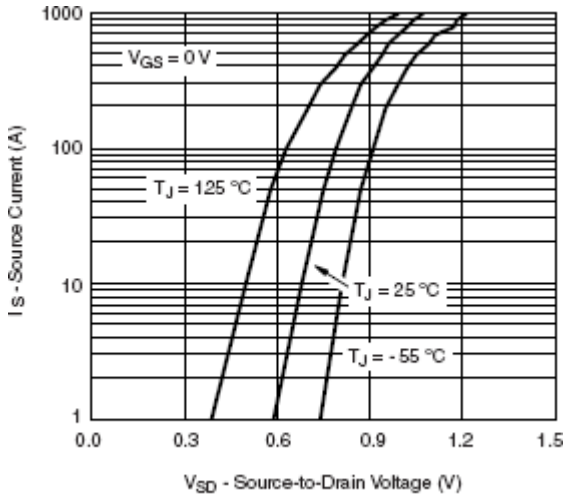
Capacitance



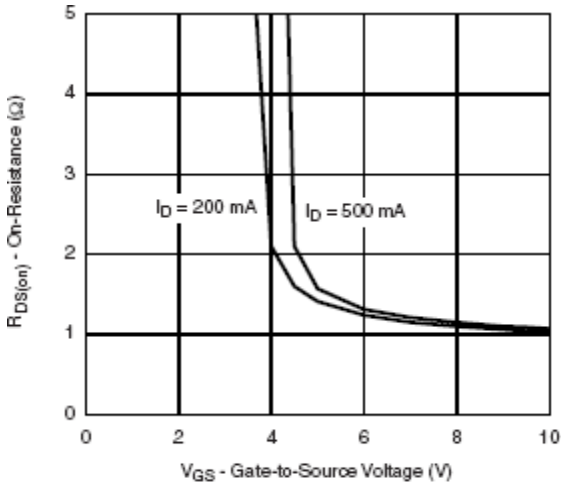
Gate Charge



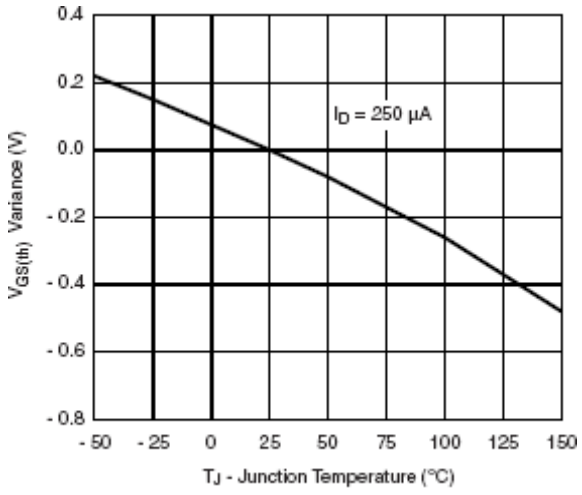
On-Resistance vs. Junction Temperature



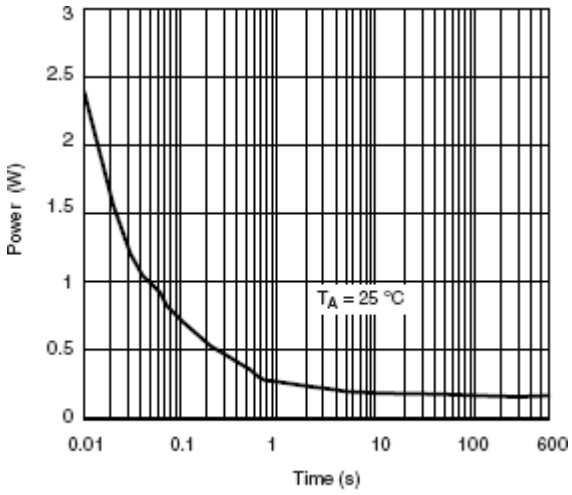
Source-Drain Diode Forward Voltage



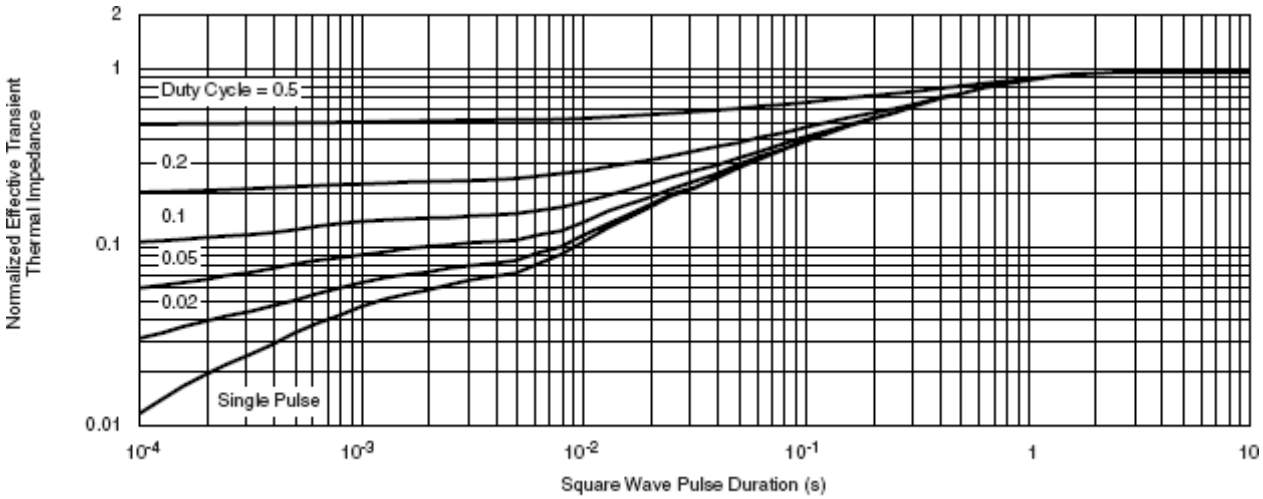
On-Resistance vs. Gate-Source Voltage



Threshold Voltage Variance Over Temperature



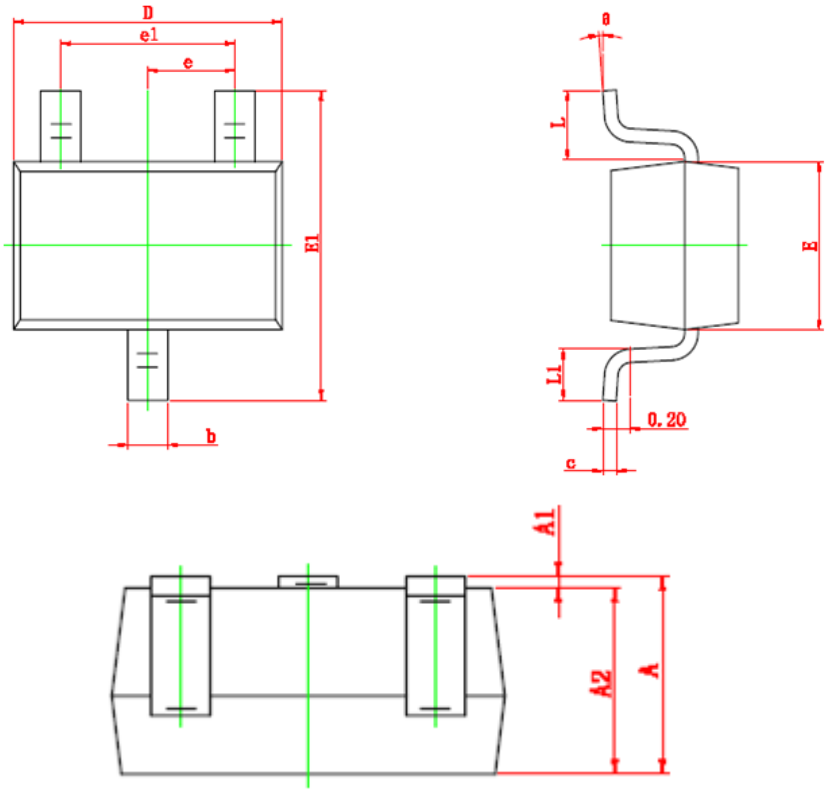
Single Pulse Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Packing Information

SOT-323



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.65 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

Notes

ACE does not assume any responsibility for use as critical components in life support devices or systems without the express written approval of the president and general counsel of ACE Electronics Co., LTD. As sued herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and shoes failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.